High Voltage, High Current Darlington Transistor Arrays

The seven NPN Darlington connected transistors in these arrays are well suited for driving lamps, relays, or printer hammers in a variety of industrial and consumer applications. Their high breakdown voltage and internal suppression diodes insure freedom from problems associated with inductive loads. Peak inrush currents to 500 mA permit them to drive incandescent lamps.

The MC1413, B with a 2.7 k Ω series input resistor is well suited for systems utilizing a 5.0 V TTL or CMOS Logic.

Features

- Pb-Free Packages are Available*
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes

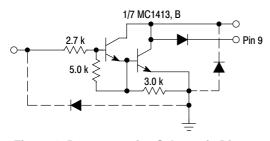


Figure 1. Representative Schematic Diagram

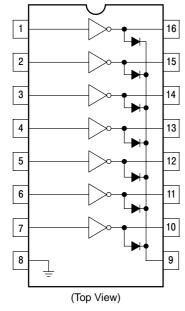


Figure 2. PIN CONNECTIONS



ON Semiconductor®

http://onsemi.com



PDIP-16 P SUFFIX CASE 648



SOIC-16 D SUFFIX CASE 751B

ORDERING INFORMATION

Device	Package	Shipping [†]			
MC1413D	SOIC-16	48 Units/Rail			
MC1413DG	SOIC-16 (Pb-Free)	48 Units/Tube			
MC1413DR2	SOIC-16	2500 Tape & Reel			
MC1413DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel			
MC1413P	PDIP-16	25 Units/Rail			
MC1413PG	PDIP-16 (Pb-Free)	25 Units/Rail			
MC1413BD	SOIC-16	48 Units/Rail			
MC1413BDG	SOIC-16 (Pb-Free)	48 Units/Rail			
MC1413BDR2	SOIC-16	2500 Tape & Reel			
MC1413BDR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel			
MC1413BP	PDIP-16	25 Units/Rail			
MC1413BPG	PDIP-16 (Pb-Free)	25 Units/Rail			
NCV1413BDR2	SOIC-16	2500 Tape & Reel			
NCV1413BDR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel			

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 5 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS ($T_A = 25^{\circ}C$, and rating apply to any one device in the package, unless otherwise noted.)

Rating	Symbol	Value	Unit
Output Voltage	Vo	50	V
Input Voltage	VI	30	V
Collector Current – Continuous	I _C	500	mA
Base Current – Continuous	Ι _Β	25	mA
Operating Ambient Temperature Range MC1413 MC1413B NCV1413B	T _A	-20 to +85 -40 to +85 -40 to +125	ů
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature	TJ	150	°C
Thermal Resistance, Junction-to-Ambient Case 648, P Suffix Case 751B, D Suffix	$R_{ heta JA}$	67 100	°C/W
Thermal Resistance, Junction-to-Case Case 648, P Suffix Case 751B, D Suffix	$R_{ heta JC}$	22 20	°C/W
Electrostatic Discharge Sensitivity (ESD) Human Body Model (HBM) Machine Model (MM) Charged Device Model (CDM)	ESD	2000 400 1500	V

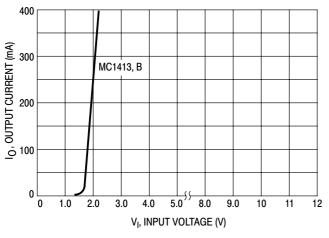
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Leakage Current $ (V_O = 50 \text{ V}, T_A = +85^{\circ}\text{C}) $ All Type $ (V_O = 50 \text{ V}, T_A = +25^{\circ}\text{C}) $ All Type		- -	- -	100 50	μΑ
$\label{eq:collector-Emitter Saturation Voltage} \tag{$I_C=350$ mA, $I_B=500$ μA}) & \text{All Type} \\ (I_C=200$ mA, $I_B=350$ μA}) & \text{All Type} \\ (I_C=100$ mA, $I_B=250$ μA}) & \text{All Type} \\ \end{aligned}$	s	- - -	1.1 0.95 0.85	1.6 1.3 1.1	V
Input Current – On Condition (V _I = 3.85 V) MC1413,	I _{I(on)}	-	0.93	1.35	mA
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	В	- - -	- - -	2.4 2.7 3.0	V
Input Current – Off Condition All Type $(I_C = 500 \ \mu A, T_A = 85^{\circ}C)$	s I _{I(off)}	50	100	_	μΑ
DC Current Gain ($V_{CE} = 2.0 \text{ V}, I_{C} = 350 \text{ mA}$)	h _{FE}	1000	_	_	-
Input Capacitance	C _I	-	15	30	pF
Turn-On Delay Time (50% E _I to 50% E _O)	t _{on}	-	0.25	1.0	μs
Turn–Off Delay Time (50% E _I to 50% E _O)	t _{off}	-	0.25	1.0	μs
Clamp Diode Leakage Current $T_A = +25^{\circ}$ $(V_R = 50 \text{ V})$ $T_A = +85^{\circ}$		_ _	- -	50 100	μΑ
Clamp Diode Forward Voltage (I _F = 350 mA)	V _F	-	1.5	2.0	V

NOTE: NCV1413B T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

TYPICAL PERFORMANCE CURVES - T_A = 25°C



400
All Types

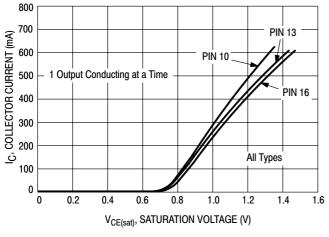
All Types

100
0 50 100 150 200 250 300 350 400

I₁, INPUT CURRENT (µA)

Figure 3. Output Current versus Input Voltage

Figure 4. Output Current versus Input Current



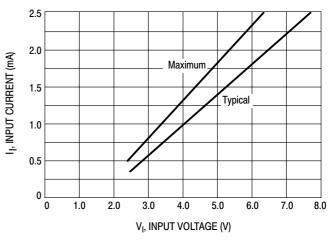


Figure 5. Typical Output Characteristics

Figure 6. Input Characteristics - MC1413, B

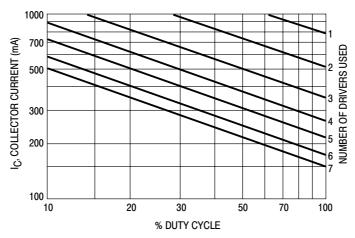
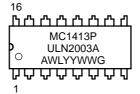
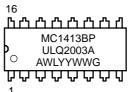


Figure 7. Maximum Collector Current versus Duty Cycle (and Number of Drivers in Use)

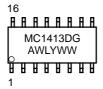
MARKING DIAGRAMS

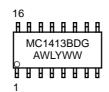
PDIP-16 P SUFFIX CASE 648

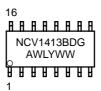












A = Assembly Location

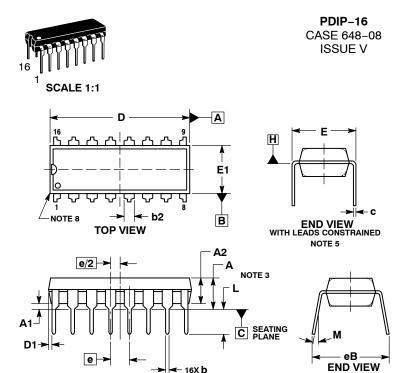
WL = Wafer Lot

YY, Y = Year

WW = Work Week

G = Pb-Free Package





16X b

| + | 0.010 M | C | A M | B M

DATE 22 APR 2015

NOTES

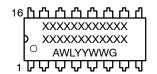
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 CONTROLLING DIMENSION: INCHES.
 DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
 DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
 DIMENSION E1 SMEASURED AT A POINT 0.015 BELOW DATUM.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
 DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- DIMENSION OF IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.

 DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.

 PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52 TYP	
С	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54	BSC
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
М		10°		10°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

= Assembly Location

WL = Wafer Lot YY = Year WW = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

:	STYLE 2	:
CATHODE	PIN 1.	COMMON DRAIN
CATHODE	2.	COMMON DRAIN
CATHODE	3.	COMMON DRAIN
CATHODE	4.	COMMON DRAIN
CATHODE	5.	COMMON DRAIN
CATHODE	6.	COMMON DRAIN
CATHODE	7.	COMMON DRAIN
CATHODE	8.	COMMON DRAIN
ANODE	9.	GATE
ANODE	10.	SOURCE
ANODE	11.	GATE
ANODE	12.	SOURCE
ANODE	13.	GATE
ANODE	14.	SOURCE
ANODE	15.	GATE
ANODE	16.	SOURCE
	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	CATHODE PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE 14. ANODE 15.

SIDE VIEW

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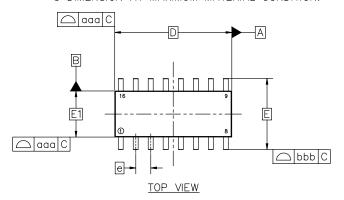


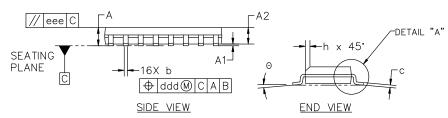
SOIC-16 9.90x3.90x1.37 1.27P CASE 751B ISSUE M

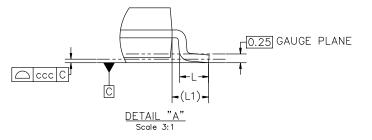
DATE 18 OCT 2024

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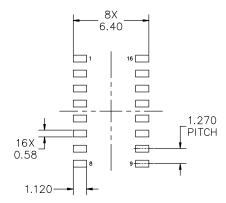
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- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS						
DIM	MIN	NOM	MAX			
А	1.35	1.55	1.75			
A1	0.10	0.18	0.25			
A2	1.25	1.37	1.50			
b	0.35	0.42	0.49			
С	0.19	0.22	0.25			
D		9.90 BSC				
E		6.00 BSC				
E1	3.90 BSC					
е	1.27 BSC					
h	0.25		0.50			
L	0.40	0.83	1.25			
L1	1.05 REF					
Θ	0.		7.			
TOLERAN	CE OF FO	RM AND	POSITION			
aaa		0.10				
bbb		0.20				
ccc		0.10				
ddd		0.25	·			
eee		0.10				



RECOMMENDED MOUNTING FOOTPRINT

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE onsemi SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

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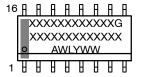
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SOIC-16 9.90x3.90x1.37 1.27P CASE 751B

ISSUE M

DATE 18 OCT 2024

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:	S	TYLE 4:	
	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
	BASE	2.	ANODE	2.	BASE. #1	2.	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER. #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	
	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH		
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)		
3.	DRAIN. #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)		
	שוויאווי, דב	٥.		٥.			
4.		3. 4.	CATHODE	3. 4.			
4. 5.	DRAIN, #2 DRAIN, #3		CATHODE CATHODE		GATE P-CH COMMON DRAIN (OUTPUT)		
5. 6.	DRAIN, #2 DRAIN, #3 DRAIN, #3	4. 5. 6.	CATHODE CATHODE CATHODE	4. 5. 6.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4	4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE	4. 5. 6. 7.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4	4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE CATHODE	4. 5. 6. 7. 8.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH		
5. 6. 7. 8.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4	4. 5. 6. 7. 8.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH		
5. 6. 7. 8. 9.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4	4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	4. 5. 6. 7. 8. 9.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3	4. 5. 6. 7. 8. 9. 10.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3	4. 5. 6. 7. 8. 9. 10. 11.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10. 11.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURGE P-CH SOURGE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH		
5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 GATE, #4 GATE, #3 SOURCE, #3 GOURCE, #3 GOURCE, #2 SOURCE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 GATE, #4 GATE, #3 SOURCE, #3 GOURCE, #3 GOURCE, #2 SOURCE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		

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